Search update (11 pp.) 5/4/4.

L Number	Hits	Search Text	DB	Time stamp
1	424	257/68	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 15:24
2	398	257/71	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 15:25
3	270	257/277	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 15:25
4	4446	257/296	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 15:25
5	877	257/298	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 15:25
6	1002	257/300	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 15:25
7	1278	257/303	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 15:25
8	3123	257/306	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 15:25
9	280	257/516	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 15:25
10	2215	257/532	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 15:25
11	227	257/906	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 15:26
12	9952	257/68 257/71 257/277 257/296 257/298 257/300 257/303 257/306 257/516 257/532 257/906	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 15:26
13	240	(257/68 257/71 257/277 257/296 257/298 257/300 257/303 257/306 257/516 257/532 257/906) and (corrugat$3 etch$3 near2 rate rippl$3) and bpsg and capacitor.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 15:27
-	0	("(boro-silicate adj glass or bpsg or germanium adj boro-silicate glass or ge-bpsg) and capacitor and dram and (corrugat$3 or rippl$3)").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 09:25

-	77	(boro-silicate adj glass or bpsg or germanium adj boro-silicate glass or ge-bpsg) and capacitor and dram and (corrugat$3 or rippl$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 14:10
-	0	((boro-silicate adj glass or bpsg or germanium adj boro-silicate glass or ge-bpsg) and capacitor and dram and (corrugat$3 or rippl$3)) and (rippl$3 or corrugat$3) near12 (capacitor adj2 wall)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 14:00
-	3	((boro-silicate adj glass or bpsg or germanium adj boro-silicate glass or ge-bpsg) and capacitor and dram and (corrugat$3 or rippl$3)) and (rippl$3 or corrugat$3) near12 (capacitor adj2 (plate or wall))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 14:00
-	43	(((borosilicate or boro-silicate) adj glass or bpsg or germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) near12 (stack$2 or alternat$3)) same capacitor and (memory adj3 (cell or device)) and dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 14:14
-	43	((((borosilicate or boro-silicate) adj glass or bpsg or germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) near12 (stack$2 or alternat$3)) same capacitor) and (memory adj3 (cell or device)) and dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 14:14
-	0	((((borosilicate or boro-silicate) adj glass or bpsg or germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) near12 (stack$2 or alternat$3)) same (rippl$3 or corrugat$3) same capacitor) and (memory adj3 (cell or device)) and dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 14:15
-	41	((((borosilicate or boro-silicate) adj glass or bpsg or germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) near12 (stack$2 or alternat$3)) same capacitor) and (rippl$3 or stack$2) and (memory adj3 (cell or device)) and dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 14:16
-	2	((((borosilicate or boro-silicate) adj glass or bpsg or germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) near12 (stack$2 or alternat$3)) same capacitor) and ((rippl$3 or stack$2) near12 (capacitor adj2 (plate or wall))) and (memory adj3 (cell or device)) and dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 14:19
-	0	((((borosilicate or boro-silicate) adj glass or bpsg or germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) near12 (stack$2 or alternat$3)) same capacitor) and ((rippl$3 or corrugat$2) near12 (capacitor adj2 (plate or wall))) and (memory adj3 (cell or device)) and dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 14:20
-	0	((((borosilicate or boro-silicate) adj glass or bpsg or germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) near12 (stack$2 or alternat$3)) same capacitor) and ((rippl$3 or corrugat$2) near12 (plate or wall)) and (memory adj3 (cell or device)) and dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 14:20
-	0	((((borosilicate or boro-silicate) adj glass or bpsg or germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) near12 (stack$2 or alternat$3)) same capacitor) and ((rippl$3 or corrugat$2) near12 (plate or wall)) and dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 14:21

-	0	(((((borosilicate or boro-silicate) adj glass or bpsg or germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) near12 (stack$2 or alternat$3)) same capacitor) and ((rippl$3 or corrugat$2) near12 (plate or wall))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 14:21
-	0	(((((borosilicate or boro-silicate) adj glass or bpsg or germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) near12 (stack$2 or alternat$3)) same capacitor) and ((rippl$3 or corrugat$2))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 14:22
-	2	(((borosilicate or boro-silicate) adj glass or bpsg or germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) near12 capacitor) and ((rippl$3 or corrugat$2) near12 capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 15:32
-	0	((germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) near12 (borosilicate or boro-silicate) adj glass) near12 (capacitance or capacitor or stacked or stacking)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 15:35
-	512	((germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) near12 (borosilicate or boro-silicate) adj glass or bpsg) near12 (capacitance or capacitor or stacked or stacking or alternate or alternating or alternatingly)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 15:37
-	51	((germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) with (borosilicate or boro-silicate) adj glass or bpsg) near12 (capacitance or capacitor or stacked or stacking or alternate or alternating or alternatingly)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 15:37
-	646	((germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) with (borosilicate or boro-silicate) adj glass or bpsg) with (capacitance or capacitor or stacked or stacking or alternate or alternating or alternatingly)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 15:37
-	51	((germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) with (borosilicate or boro-silicate) adj glass or bpsg) near10 (capacitance or capacitor or stacked or stacking or alternate or alternating or alternatingly)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 15:37
-	38	((germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) with (borosilicate or boro-silicate) adj glass or bpsg) near10 (capacitance or capacitor or stacked or stacking or alternate or alternating or alternatingly) and dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 15:38
-	30	((germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) with (borosilicate or boro-silicate) adj glass or bpsg) near10 (capacitance or capacitor or stacked or stacking or alternate or alternating or alternatingly) and dram	USPAT	2002/02/08 15:46
-	0	((germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) with (borosilicate or boro-silicate) adj glass or bpsg) near10 (capacitance or capacitor or stacked or stacking or alternate or alternating or alternatingly) and dram and corrugat$3	USPAT	2002/02/08 15:40
-	0	((germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) with (borosilicate or boro-silicate) adj glass or bpsg) near10 (capacitance or capacitor or stacked or stacking or alternate or alternating or alternatingly) and dram and corrugat$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 15:40

-	0	((germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) with (borosilicate or boro-silicate) adj glass or bpsg) near10 (capacitance or capacitor or stacked or stacking or alternate or alternating or alternatingly) and dram and (rippl$3 or corrugat$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 15:41
-	0	((germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) with (borosilicate or boro-silicate) adj glass or bpsg) near10 (capacitance or capacitor or stacked or stacking or alternate or alternating or alternatingly) and dram and (rippl$3 or corrugat$3 or standing adj wav$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/08 15:42
-	30	(ge-bpsg and (borosilicate or boro-silicate) adj glass or bpsg) near10 (capacitance or capacitor or stacked or stacking or alternate or alternating or alternatingly) and dram	USPAT	2002/02/08 15:47
-	0	(ge-bpsg and (borosilicate or boro-silicate) adj glass or bpsg) near10 (capacitance or capacitor or stacked or stacking or alternate or alternating or alternatingly) and (rippl$3 or corrugat$3) and dram	USPAT	2002/02/08 15:48
-	0	(ge-bpsg and (borosilicate or boro-silicate) adj glass or bpsg) near10 (capacitance or capacitor or stacked or stacking or alternate or alternating or alternatingly) and (rippl$3 or corrugat$3)	USPAT	2002/02/08 15:49
-	0	(ge-bpsg near10 (capacitance or capacitor or stacked or stacking or alternate or alternating or alternatingly)) and (rippl$3 or corrugat$3)	USPAT	2002/02/08 15:50
-	0	(ge-bpsg or germanium-boro-phospho adj silicate adj glass or germanium adj boro-phospho adj silicate adj glass or germanium-boro-phospho-silicate adj glass or germanium adj boro adj phospho adj silicate adj glass) same (stacked or stacking or alternating or alternate or alternately or multi-layer or multi adj layer or laminat$3)	USPAT	2002/02/08 15:56
-	2	ge-bpsg or germanium-boro-phospho adj silicate adj glass or germanium adj boro-phospho adj silicate adj glass or germanium-boro-phospho-silicate adj glass or germanium adj boro adj phospho adj silicate adj glass or ge-bpsg	USPAT	2002/02/08 15:56
-	1	5648175.pn.	USPAT	2002/02/09 10:09
-	14	(("5061650") or ("5240871") or ("5300801") or ("5466627") or ("5637523") or ("5656536") or ("5827783") or ("5843822") or ("5879987") or ("6025225") or ("6027970") or ("6028763") or ("6060355") or ("6074926")).PN.	USPAT	2002/02/09 10:14
-	0	((("5061650") or ("5240871") or ("5300801") or ("5466627") or ("5637523") or ("5656536") or ("5827783") or ("5843822") or ("5879987") or ("6025225") or ("6027970") or ("6028763") or ("6060355") or ("6074926")).PN.) and corrugat$3 and capacit$3 and bpsg and ge-bpsg	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 10:14
-	0	((("5061650") or ("5240871") or ("5300801") or ("5466627") or ("5637523") or ("5656536") or ("5827783") or ("5843822") or ("5879987") or ("6025225") or ("6027970") or ("6028763") or ("6060355") or ("6074926")).PN.) and capacit$3 and bpsg and ge-bpsg	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 10:14

-	118	((increase near5 capacitance) near5 surface) near5 (rough$5 or etch$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 10:18
-	0	((increase near5 capacitance) near5 surface) near5 (rough$5 or etch$3) and "L14"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 10:17
-	0	((increase near5 capacitance) near5 surface) near5 (rough$5 or etch$3) and "L14"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 10:17
-	131	(((("5061650") or ("5240871") or ("5300801") or ("5466627") or ("5637523") or ("5656536") or ("5827783") or ("5843822") or ("5879987") or ("6025225") or ("6027970") or ("6028763") or ("6060355") or ("6074926")).PN.) or (((increase near5 capacitance) near5 surface) near5 (rough$5 or etch$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 10:18
-	35	(((("5061650") or ("5240871") or ("5300801") or ("5466627") or ("5637523") or ("5656536") or ("5827783") or ("5843822") or ("5879987") or ("6025225") or ("6027970") or ("6028763") or ("6060355") or ("6074926")).PN.) or (((increase near5 capacitance) near5 surface) near5 (rough$5 or etch$3))) and ((increas$3 near5 capacitance) near5 etch$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 10:21
-	6	((((("5061650") or ("5240871") or ("5300801") or ("5466627") or ("5637523") or ("5656536") or ("5827783") or ("5843822") or ("5879987") or ("6025225") or ("6027970") or ("6028763") or ("6060355") or ("6074926")).PN.) or (((increase near5 capacitance) near5 surface) near5 (rough$5 or etch$3))) and ((increas$3 near5 capacitance) near5 etch$3)) and bpsg	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 10:41
-	2	(((((("5061650") or ("5240871") or ("5300801") or ("5466627") or ("5637523") or ("5656536") or ("5827783") or ("5843822") or ("5879987") or ("6025225") or ("6027970") or ("6028763") or ("6060355") or ("6074926")).PN.) or (((increase near5 capacitance) near5 surface) near5 (rough$5 or etch$3))) and ((increas$3 near5 capacitance) near5 etch$3)) and bpsg) and germanium	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 10:42
-	166	different adj etch$3 adj2 rates and bpsg	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 10:42
-	0	(different adj etch$3 adj2 rates near5 bpsg) near5 capacitance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 10:43
-	11	different adj etch$3 adj2 rates near5 bpsg	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 11:09

-	507	etch$3 adj rate same bpsg	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 11:09
-	318	etch$3 adj rate with bpsg	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 11:09
-	1	etch$3 adj rate with (bpsg and (ge-bpsg or germanium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 16:42
-	3	5827783.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 17:35
-	68	(bst same capacitor same dielectric) and memory adj device.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 17:36
-	25	(bst near6 capacitor near6 dielectric) and memory adj device.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 17:55
-	2	((si-ge or silicon-germanium) same capacitor same dielectric) and memory adj device.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 22:09
-	2	5930106.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 18:01
-	4791	((257/68) or (257/71) or (257/277) or (257/296) or (257/298) or (257/300) or (257/303) or (257/306) or (257/516) or (257/532) or (257/906)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/17 09:57
-	3	(((("257/68") or ("257/71") or ("257/277") or ("257/296") or ("257/298") or ("257/300") or ("257/303") or ("257/306") or ("257/516") or ("257/532") or ("257/906")).CCLS.) and bpsg and germanium and capacitor and memory adj2 device.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 22:11
-	3	5827783.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 22:12
-	3	5804506.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 22:13
-	3	5889696.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/09 22:13
-	2	5889696.pn.	USPAT; DERWENT	2002/02/10 09:09
-	2	5930106.pn.	USPAT; DERWENT	2002/02/10 09:10

-	0	(323/539).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/08 16:56
-	1364	(band adj gap or bandgap) adj reference near5 voltage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/08 16:57
-	275	(bandgap) adj reference near5 voltage and bipolar adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/08 16:58
-	155	(327/539).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/08 16:58
-	2	("5804506").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/05 11:50
-	2	("5972769").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/05 10:56
-	2	("6376303").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/05 10:57
-	2	("5827783").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/05 13:11
-	5502	((257/68) or (257/71) or (257/277) or (257/296) or (257/298) or (257/300) or (257/303) or (257/306) or (257/516) or (257/532) or (257/906)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/05 13:12
-	13	(((257/68) or (257/71) or (257/277) or (257/296) or (257/298) or (257/300) or (257/303) or (257/306) or (257/516) or (257/532) or (257/906)).CCLS.) and corrugat$3 near15 (capacitor or capacitance) and memory.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/05 13:13
-	3	((corrugation corrugated) near6 (sidewall side adj wall)) and stacked adj capacitor and germanium and (BPSG boro-phosphosilicate adj glass)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 13:16
-	381	(boro-phosphosilicate adj glass BPSG boro adj phospho-silicate adj glass) and germanium and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 13:17
-	3	(boro-phosphosilicate adj glass BPSG boro adj phospho-silicate adj glass) and germanium and capacitor and (corrugated corrugation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 13:18
-	109	(boro-phosphosilicate adj glass BPSG boro adj phospho-silicate adj glass) and germanium and stacked adj capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 13:19

–	22	(boro-phosphosilicate adj glass BPSG boro adj phospho-silicate adj glass) and germanium and stacked adj capacitor.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 13:22
–	0	("6651946").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 13:22
–	2	("6346455").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 13:23
–	1	"6074926".PN.	USPAT	2003/05/27 13:23
–	1	"6060355".PN.	USPAT	2003/05/27 13:24
–	30	(US-5874756-$ or US-6008515-$ or US-4716548-$ or US-5545585-$ or US-6124607-$ or US-6190992-$ or US-6303430-$ or US-5889696-$ or US-5930106-$ or US-6376303-$ or US-5804506-$ or US-6159792-$ or US-5656536-$ or US-5648175-$ or US-6087694-$ or US-6150208-$ or US-4894696-$ or US-5250458-$ or US-5519238-$ or US-5213992-$ or US-5438011-$ or US-4855953-$ or US-4845539-$ or US-5471087-$ or US-5835337-$ or US-5972769-$).did. or (US-4786954-$).did. or (US-20010006449-$).did. or (EP-507683-$).did. or (US-5889696-$).did.	USPAT; US-PGPUB; EPO; DERWENT	2003/05/27 13:29
–	1	((US-5874756-$ or US-6008515-$ or US-4716548-$ or US-5545585-$ or US-6124607-$ or US-6190992-$ or US-6303430-$ or US-5889696-$ or US-5930106-$ or US-6376303-$ or US-5804506-$ or US-6159792-$ or US-5656536-$ or US-5648175-$ or US-6087694-$ or US-6150208-$ or US-4894696-$ or US-5250458-$ or US-5519238-$ or US-5213992-$ or US-5438011-$ or US-4855953-$ or US-4845539-$ or US-5471087-$ or US-5835337-$ or US-5972769-$).did. or (US-4786954-$).did. or (US-20010006449-$).did. or (EP-507683-$).did. or (US-5889696-$).did.) and haller.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 13:39
–	2	("6346455").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 14:15
–	4	BPSG near2 layer and Ge-BPSG near2 layer and semiconductor.ti,ab,clm. and memory.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 14:20
–	4	BPSG near2 layer and Ge-BPSG near2 layer and semiconductor.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 14:21
–	1	(boro-phospho-silicate boro-phosphosilicate boro adj phosphosilicate BPSG) near2 layer and (germanium-doped near4 (boro-phospho-silicate BPSG Ge-BPSG) near4 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 14:48

-	664	(PSG phosphorus near2 doped adj glass) and germanium and (BPSG boron PBSG)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 14:50
-	280	(PSG phosphorus near2 doped adj glass) and germanium and (BPSG boron PBSG) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 14:56
-	114	(PSG phosphorus near2 doped adj glass) and germanium and (BPSG boron PBSG) and capacitor.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 15:02
-	16	germanium near12 (BPSG PBSG boro$1phoshosilicate) and capacitor.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 15:09
-	14	(("5061650") or ("5240871") or ("5300801") or ("5466627") or ("5637523") or ("5656536") or ("5827783") or ("5843822") or ("5879987") or ("6025225") or ("6027970") or ("6028763") or ("6060355") or ("6074926")).PN.	USPAT	2003/05/27 15:21
-	0	("etch near2 selectivity and (corrugation corrugated) and capacitor").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 15:23
-	40	etch near2 selectivity and (corrugation corrugated) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 15:48
-	21	(etch near2 selectivity and (corrugation corrugated) and capacitor) and ("1:4" "4:1")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 15:48
-	2	("5827783").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/27 20:00
-	6	"5827783"	USPAT	2003/11/13 14:59
-	1	("5827783").PN.	USPAT	2003/11/13 15:00
-	1	("5804506").PN.	USPAT	2003/11/13 15:00
-	2	("5827783").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 19:41
-	2	("5804506").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 19:41
-	6351	((257/68) or (257/71) or (257/277) or (257/296) or (257/298) or (257/300) or (257/303) or (257/306) or (257/516) or (257/532) or (257/906)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:23
-	20	(((257/68) or (257/71) or (257/277) or (257/296) or (257/298) or (257/300) or (257/303) or (257/306) or (257/516) or (257/532) or (257/906)).CCLS.) and (corrugated corrugation) near12 capacitor and (capacitor adj cell dram adj cell memory adj cell semiconductor near2 (device element)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:49

–		5	(boro-phospho-silicate boro adj phospho-silicate BSG BFSG BSG:F boro adj phospho adj silicate boro adj phospho adj silicate) and (corrugated corrugation) near12 capacitor and (capacitor adj cell dram adj cell memory adj cell semiconductor near2 (device element)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:57
–		5	(boro-phospho-silicate boro adj phospho-silicate BSG BFSG BSG:F boro adj phospho adj silicate boro adj phospho adj silicate) and (corrugated-trench adj capacitor ccc adj structure (corrugated corrugation) near12 capacitor) and (capacitor adj cell dram adj cell memory adj cell semiconductor near2 (device element)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:58
–		7	corrugated adj capacitor and wall and (bpsg boro adj phospho adj silicate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/17 08:28
–		10	(corrugated-trench adj capacitor ccc adj structure (corrugated corrugation) near12 capacitor) and wall and (bpsg boro adj phospho adj silicate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/17 08:33
–		4	(corrugated-trench adj capacitor ccc adj structure (corrugated corrugation) near12 capacitor) and wall near12 (bpsg boro adj phospho adj silicate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/17 08:41
–		8	(BPSG boro adj phospho adj silicate) near12 wall near12 capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/17 08:56
–		8	(BPSG boro adj phospho adj silicate) near12 wall near12 capacitor and (insulating dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/17 08:57
–		6351	((257/68) or (257/71) or (257/277) or (257/296) or (257/298) or (257/300) or (257/303) or (257/306) or (257/516) or (257/532) or (257/906)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/17 10:12
–		3	(((257/68) or (257/71) or (257/277) or (257/296) or (257/298) or (257/300) or (257/303) or (257/306) or (257/516) or (257/532) or (257/906)).CCLS.) and corrugated near6 capacitor and (boro adj phospho adj silicate BPSG)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/17 10:12
–		2	("5827783").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/03 13:57
–		2	("6097053").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/03 13:58
–		2	("5804506").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 15:24
–		7	(("5519238") or ("5623243") or ("5830793")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/03 14:31

-		5	(bpsg near3 (germanium ge) ge-bpsg) and capacitor and (corrugate corrugated corrugating corrugation corrugates)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 10:00
-		5	(bpsg near3 (germanium ge) ge-bpsg) and capacitor and (corrugate corrugated corrugating corrugation corrugates ripple rippled ripples rippling)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 10:02
-		25	(bpsg near3 (germanium ge) ge-bpsg) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 10:02
-		20	((bpsg near3 (germanium ge) ge-bpsg) and capacitor) not ((bpsg near3 (germanium ge) ge-bpsg) and capacitor and (corrugate corrugated corrugating corrugation corrugates ripple rippled ripples rippling))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 10:35
-		21	((bpsg near3 (germanium ge) ge-bpsg gepsg) and capacitor) not ((bpsg near3 (germanium ge) ge-bpsg) and capacitor and (corrugate corrugated corrugating corrugation corrugates ripple rippled ripples rippling))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 10:36
-		6	((bpsg near3 (germanium ge) ge-bpsg gepsg) and capacitor) not (((bpsg near3 (germanium ge) ge-bpsg) and capacitor) not ((bpsg near3 (germanium ge) ge-bpsg) and capacitor and (corrugate corrugated corrugating corrugation corrugates ripple rippled ripples rippling)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 10:36